

N-channel TrenchMOS logic level FET 26 May 2016

Product data sheet

1. General description

Logic level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with Vgst(th) rating of greater than 0.5V at 175 °C

3. Applications

- 12V, 24V and 48V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	100	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	263	W
Static characte	eristics	·	1	1			
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u>		-	7.49	9.3	mΩ
Dynamic characteristics							
Q _{GD}	gate-drain charge	V _{GS} = 5 V; I _D = 25 A; V _{DS} = 80 V; Fig. 13; Fig. 14		-	34	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G-UTA
mb	D	mounting base; connected to drain	D2PAK (SOT404)	mbb076 S

6. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
BUK969R3-100E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404		

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK969R3-100E	BUK969R3-100E

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	100	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	100	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-10	10	V
		$T_j \le 175 \ ^{\circ}C; Pulsed$	[1][2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	263	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 2</u>		-	100	А
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 2</u>		-	71	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 3		-	405	А
T _{stg}	storage temperature			-55	175	°C
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Symbol	Parameter	Conditions		Min	Max	Unit
Tj	junction temperature			-55	175	°C
Source-drai	in diode		1			
I _S	source current	T _{mb} = 25 °C		-	100	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	405	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{split} I_D &= 100 \text{ A}; \text{V}_{\text{sup}} \leq 100 \text{ V}; \text{R}_{\text{GS}} = 50 \Omega; \\ \text{V}_{\text{GS}} &= 5 \text{ V}; \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped}; \\ \hline \text{Fig. 4} \end{split}$	[3][4]	-	219	mJ

- Accumulated pulse duration up to 50 hours delivers zero defect ppm [1]
- [2] Significantly longer life times are achieved by lowering T_i and or V_{GS}

Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. Refer to application note AN10273 for further information.

[3] [4]

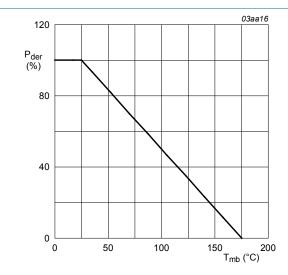
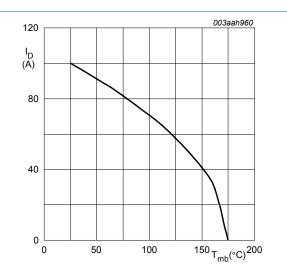


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

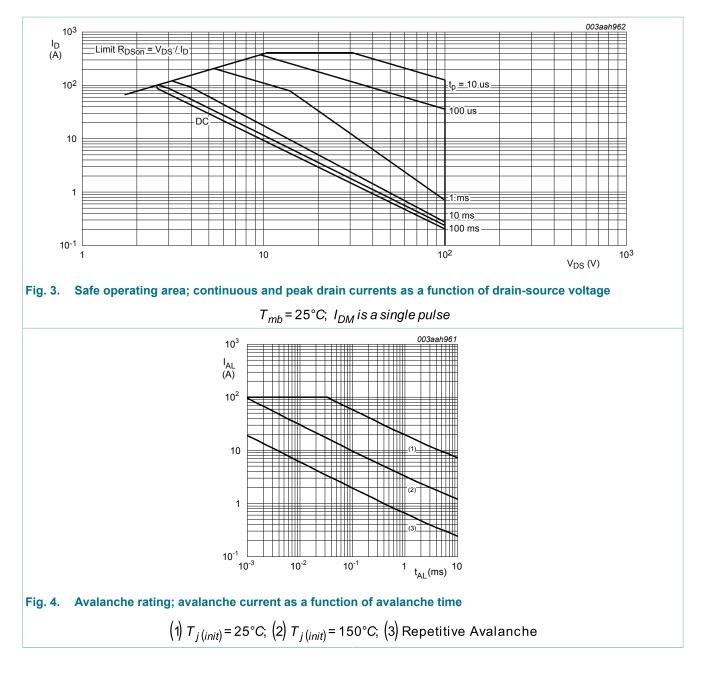
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$



Continuous drain current as a function of Fig. 2. mounting base temperature

 $V_{GS} \ge 5V$

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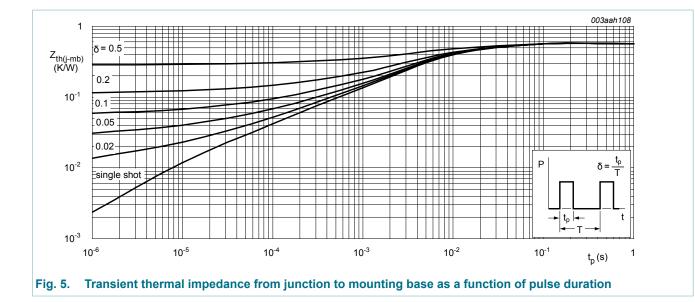
9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	0.57	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	50	-	K/W

Table 6. Thermal characteristics

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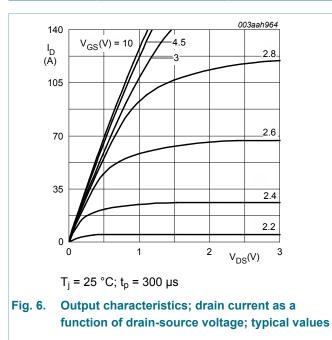


10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Static chara	acteristics	1					
V _{(BR)DSS}	drain-source	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = 25 \ ^{\circ}C$	100	-	-	V	
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	90	-	-	V	
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.1	V	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	2.45	V	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	0.5	-	-	V	
I _{DSS} drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.06	1	μA		
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA	
I _{GSS} gate lea	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA	
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA	
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u>	-	7.49	9.3	mΩ	
resistance		resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u>	-	7.23	8.9	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 11	-	-	25.7	mΩ	
Dynamic ch	naracteristics	· · ·					
Q _{G(tot)}	total gate charge	I_D = 25 A; V_{DS} = 80 V; V_{GS} = 5 V;	-	94.3	-	nC	
Q _{GS}	gate-source charge	Fig. 13; Fig. 14	-	15.2	-	nC	

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{GD}	gate-drain charge		-	34	-	nC
C _{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;	-	8739	11650	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	499	599	pF
C _{rss}	reverse transfer capacitance		-	312	427	pF
t _{d(on)}	turn-on delay time	V_{DS} = 80 V; R _L = 3.2 Ω; V _{GS} = 5 V;	-	39.5	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	95.1	-	ns
t _{d(off)}	turn-off delay time		-	118	-	ns
t _f	fall time	-	-	93.4	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to center of die	-	2.5	-	nH
L _S	internal source inductance	from source lead to source bonding pad	-	7.5	-	nH
Source-dra	in diode					,
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 20 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;	-	55.5	-	ns
Qr	recovered charge	V _{DS} = 25 V	-	142	-	nC



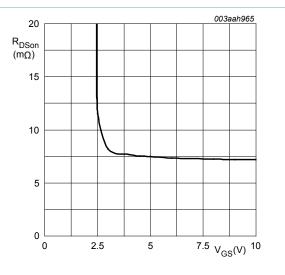
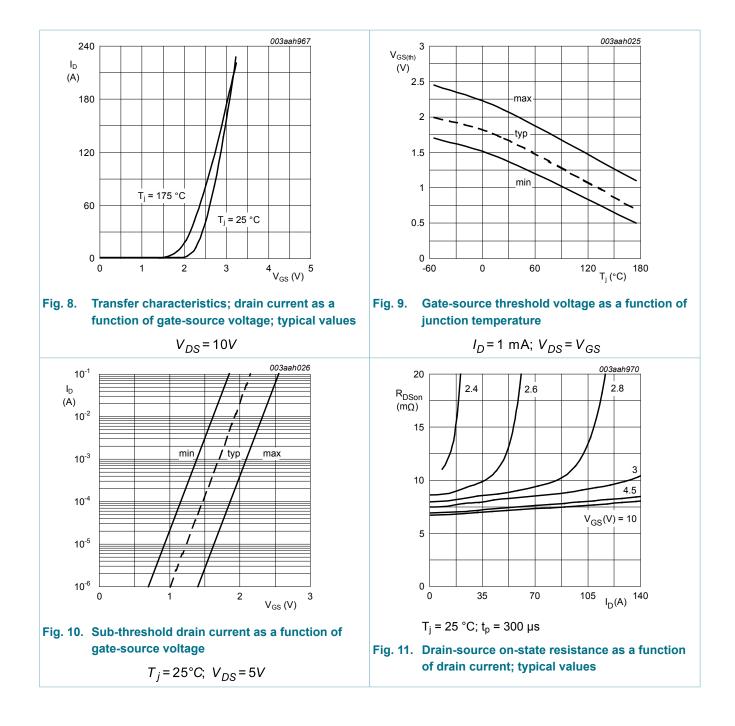


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; I_D = 25A$

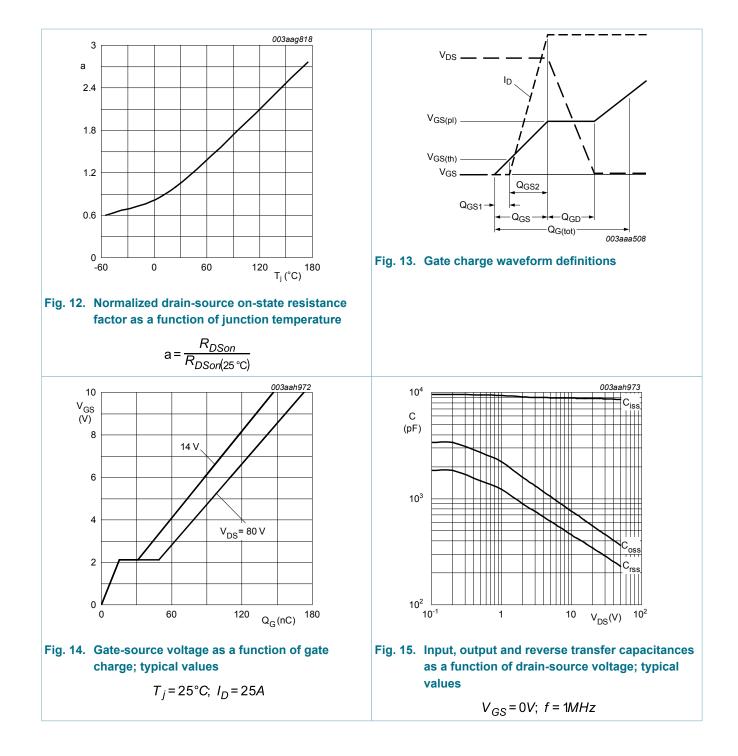
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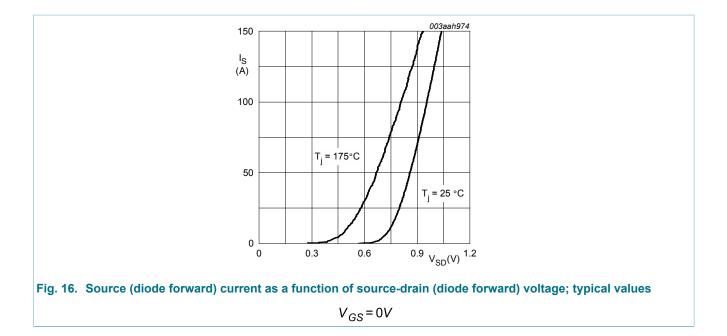
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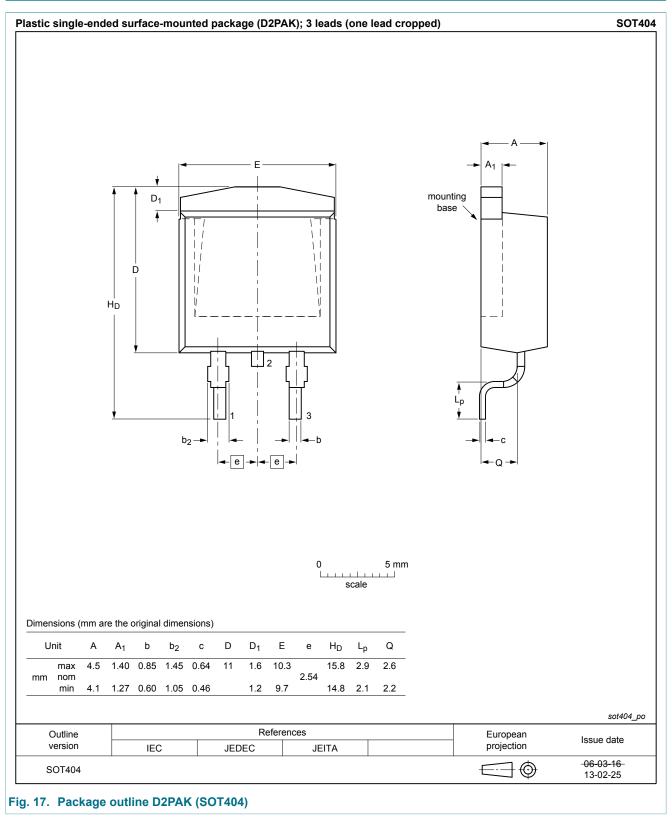
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11. Package outline



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Product data sheet

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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